CLAIMS

1	1. A semiconductor structure comprising:
2	a semiconductor substrate;
3	at least one first crystalline epitaxial layer on said substrate, said first layer having a
4	surface which is planarized; and
5	at least one second crystalline epitaxial layer on said at least one first layer.
1	
1	2. The structure of claim 1, wherein said at least one first crystalline epitaxial layer is
2	lattice mismatched.
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	3. The structure of claim 1, wherein said at least one second crystalline epitaxial layer is
2	lattice mismatched.
	4. The structure of claim 1, wherein said first and second crystalline epitaxial layers are
2	lattice mismatched.
1	
1	5. The structure of claims 2, wherein said at least one first layer comprises a composition
2	graded relaxed epitaxial region.
1	
1	6. The structure of claims 3, wherein said at least one second layer comprises a
2	composition graded relaxed epitaxial region.
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alloys greater than 75% are grown at 550°C.

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26. The structure of claim 25, wherein said graded region is planarized by chemical-

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mechanical polishing.

1	27. A semiconductor structure comprising:
2	a semiconductor substrate;
3	a first layer having a graded region grown on said substrate, compressive strain being
4	incorporated in said graded region to offset the tensile strain that is incorporated during thermal
5	processing, said first layer having a surface which is planarized; and
6	a second layer provided on said first layer.
1	
	28. A method of fabricating a semiconductor structure comprising:
2	providing a semiconductor substrate;
	providing at least one first crystalline epitaxial layer on said substrate; and
4	planarizing the surface of said first layer.
1	
	29. The method of claim 28 further comprising providing at least one second crystalline
2	epitaxial layer on said first layer.
1	
1.	30. The method of claim 28, wherein said step of providing said first layer comprises
2	growing a GeSi relaxed graded region on said substrate.
1	

31. The method of claim 30 further comprising incorporating compressive strain in said

grade region to offset tensile strain incorporated during thermal processing.

550°C.

- 32. The method of claim 31, wherein said step of incorporating compressive strain comprises decreasing the growth temperature as Ge concentration increases in said graded region.
- 33. The method of claim 32, wherein said step of incorporating compressive strain comprises growing alloys of Ge_xSi_{1-x} from x=0 to about x≈35% at 750°C, growing alloys from x=35 to about x≈75% at between 650°C and 750°C, and growing alloys greater than 75% at
 - 34. The method of claim 28, wherein said step of planarizing comprises chemical-mechanical polishing.